

CTLTVS6V2

**SURFACE MOUNT SILICON
TRANSIENT VOLTAGE SUPPRESSOR**



www.centrasemi.com



DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLTVS6V2 is a low leakage, fast response silicon TVS packaged in an ultra small, ultra low profile TLM2D3D6 surface mount case. This device is designed to protect sensitive equipment against ESD damage.

MARKING CODE: S

APPLICATIONS:

- User interface protection
- Voltage rail protection
- Data line protection
- Voltage clamping

FEATURES:

- Ultra small, ultra low profile 0.3mm x 0.6mm x 0.3mm TLP™ leadless surface mount package
- High peak pulse current capability
- Low leakage current
- 15kV ESD protection

MAXIMUM RATINGS: (T_A=25°C)

Peak Power Dissipation (8x20μs)
ESD Voltage (IEC 61000-4-2, Air)
Operating and Storage Junction Temperature

SYMBOL

P_{PK}
V_{ESD}
T_J, T_{stg}

UNITS

W
kV
°C

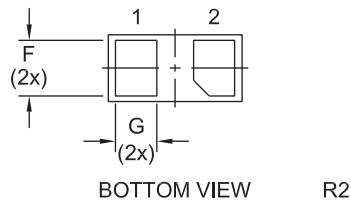
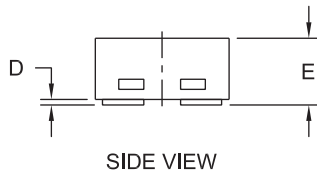
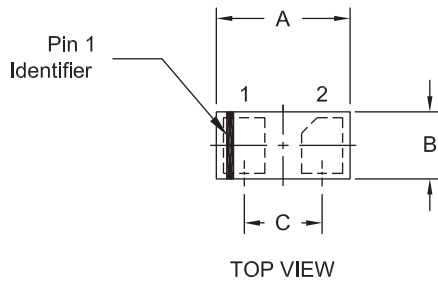
ELECTRICAL CHARACTERISTICS: (T_A=25°C) V_F=1.0V MAX @ I_F=10mA

Maximum Reverse Stand-off Voltage V _{RWM}	Breakdown Voltage			Test Current I _T	Maximum Reverse Leakage Current I _R @ V _{RWM}	Maximum Clamping Voltage V _C @ I _{PP}	Peak Pulse Current I _{PP}	Typical Junction Capacitance @ 0V Bias C _J
	MIN V	NOM V	MAX V					
V				mA	μA	V	A	pF
4.0	5.8	6.2	6.6	5.0	1.0	10.7	3.0	25

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TLM2D3D6 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.022	0.026	0.55	0.65
B	0.010	0.014	0.25	0.35
C	0.014		0.35	
D	0.000	0.002	0.00	0.05
E	0.011	0.013	0.28	0.32
F	0.008	0.012	0.20	0.30
G	0.005	0.009	0.13	0.24

TLM2D3D6 (REV: R2)

LEAD CODE:
 1) Cathode
 2) Anode

MARKING CODE: S

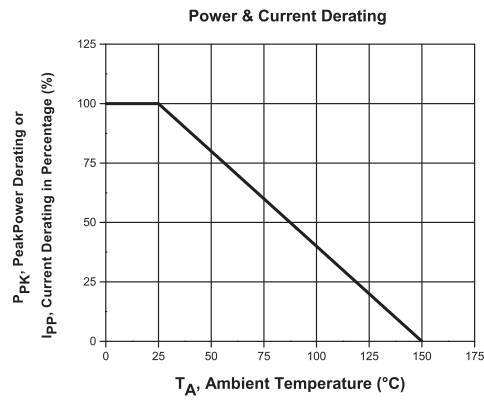
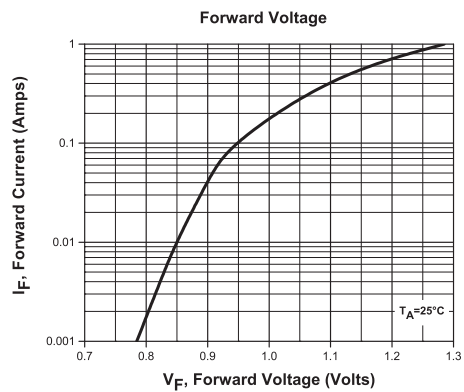
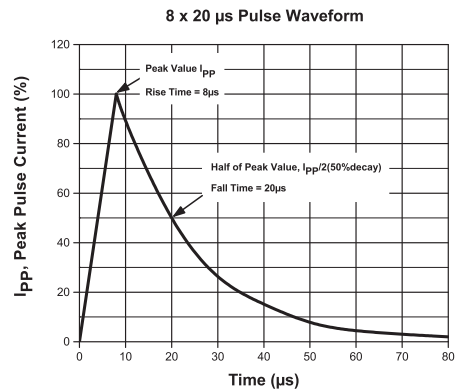
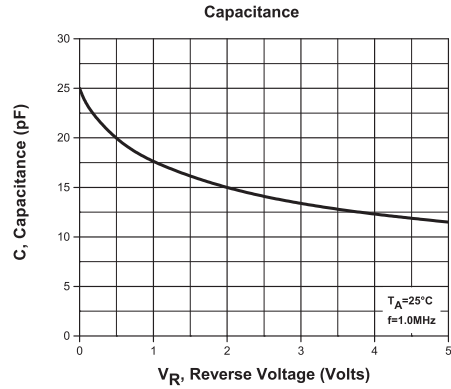
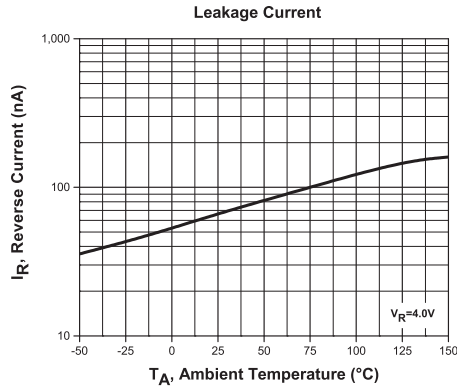
R2

R1 (23-January 2013)

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TYPICAL ELECTRICAL CHARACTERISTICS



R1 (23-January 2013)